

# Band alignment in CdS- $\alpha$ -Te van der Waals heterostructures for photocatalytic applications: Influence of biaxial strain and electric field

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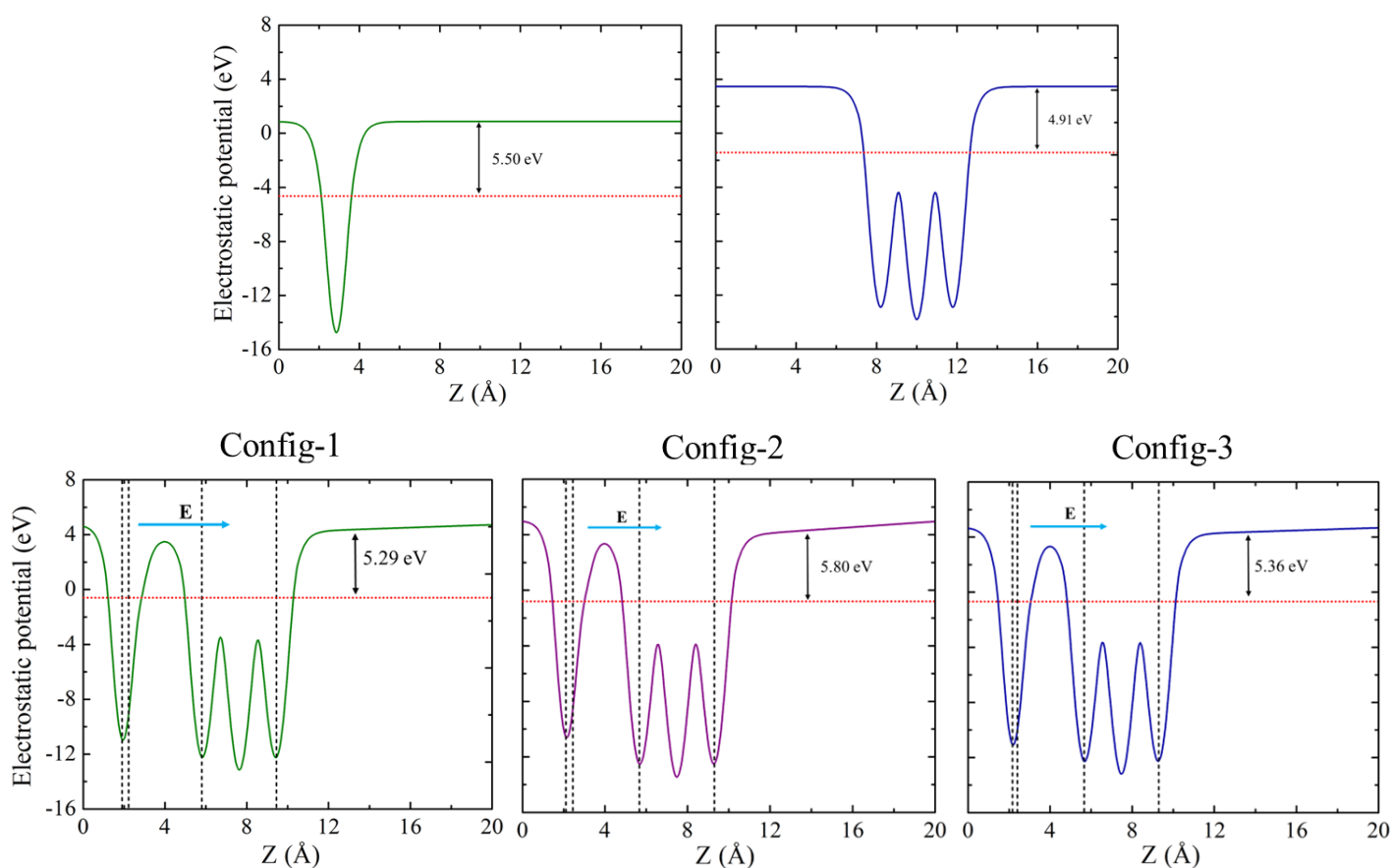
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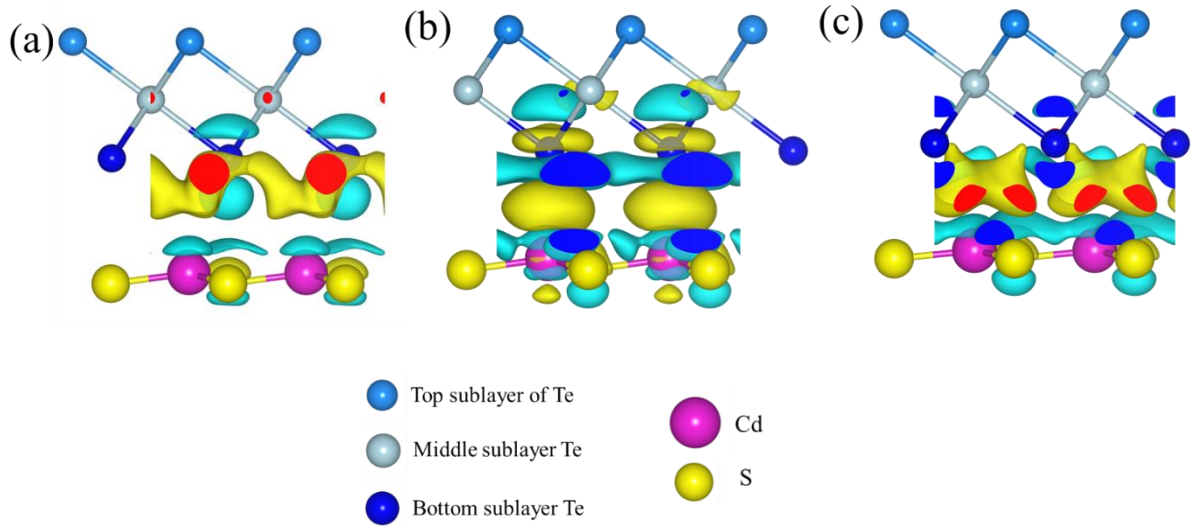
## Supplementary Information



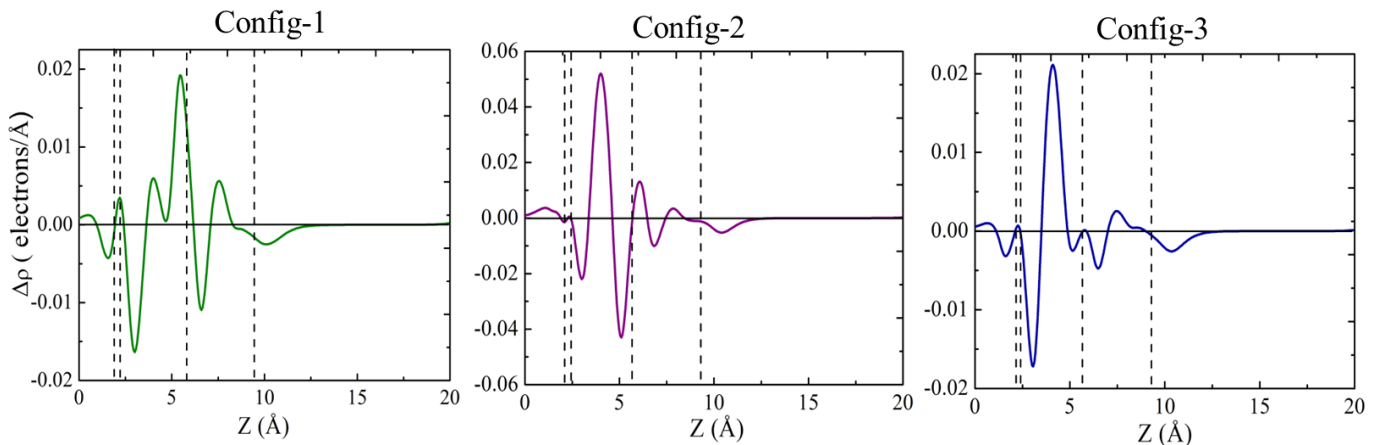
SFig. 1: The electrostatic potential of the CdS,  $\alpha$ -Te SLs and the three configurations of the CdS-  $\alpha$ -Te heterostructure. The vertical dashed lines represent the boundaries of the CdS (left) and  $\alpha$ -Te (right) layers. The light blue arrow denotes the direction of the built-in electric field  $E$ . The red dotted line represents the Fermi-level. The results presented here are within the GGA approximation.

STable 1: Vacuum level and work functions of CdS and  $\alpha$ -Te SLs and CdS- $\alpha$ -Te heterostructure.

Structure	Vacuum level (eV)	Work function (eV)
CdS	0.86	5.50
$\alpha$ -Te	3.44	4.91
Config-1	4.71	5.29
Config-2	4.98	5.80
Config-3	4.68	5.36



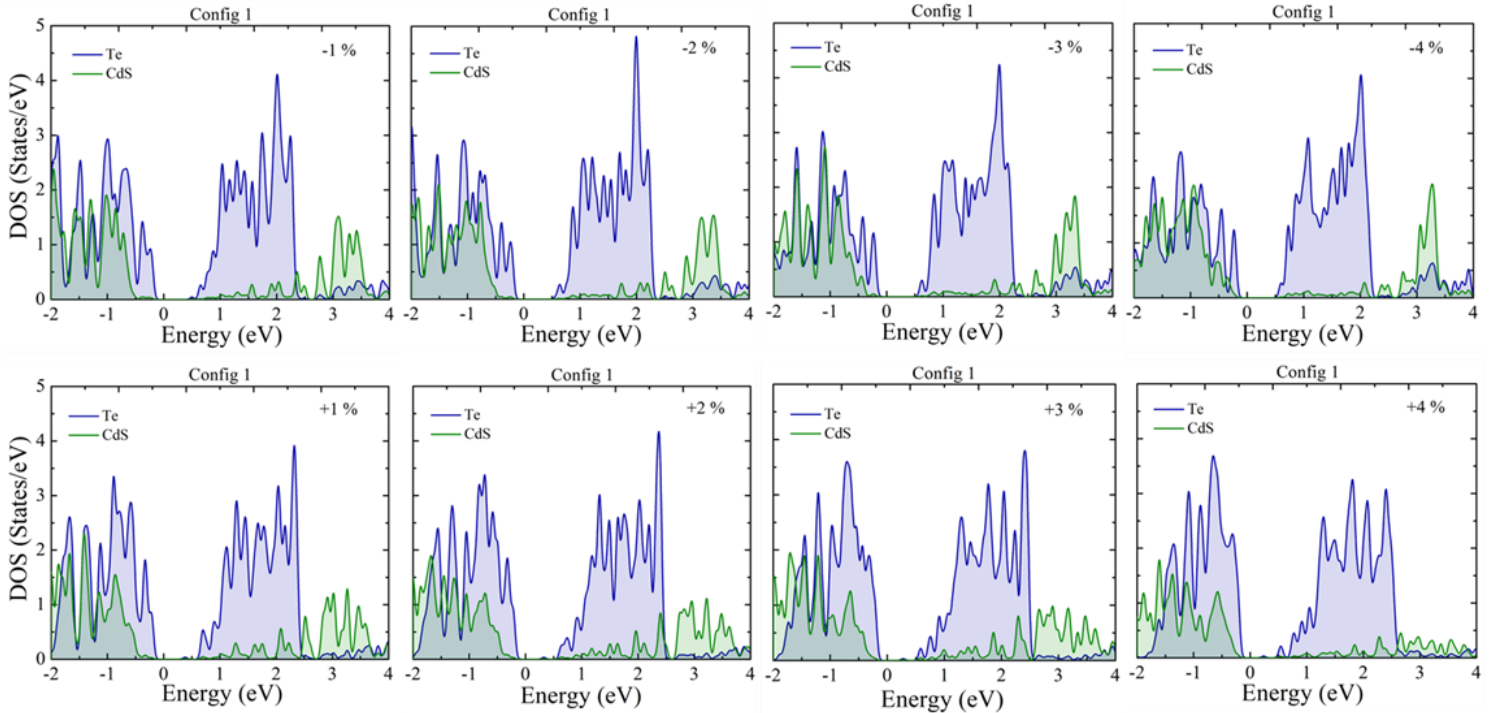
SFig. 2: Differential electron density representation in (a) config-1, (b) config-2 and (c) config-3 of the CdS- $\alpha$ -Te heterostructure with isosurface level  $0.0002 \text{ e}/\text{\AA}^3$ . The yellow and cyan colored regions around the atoms represents the electron accumulation and depletion respectively. Note, that the red and dark blue areas solely denote cross-sections of yellow and cyan regions with the plane of the picture.

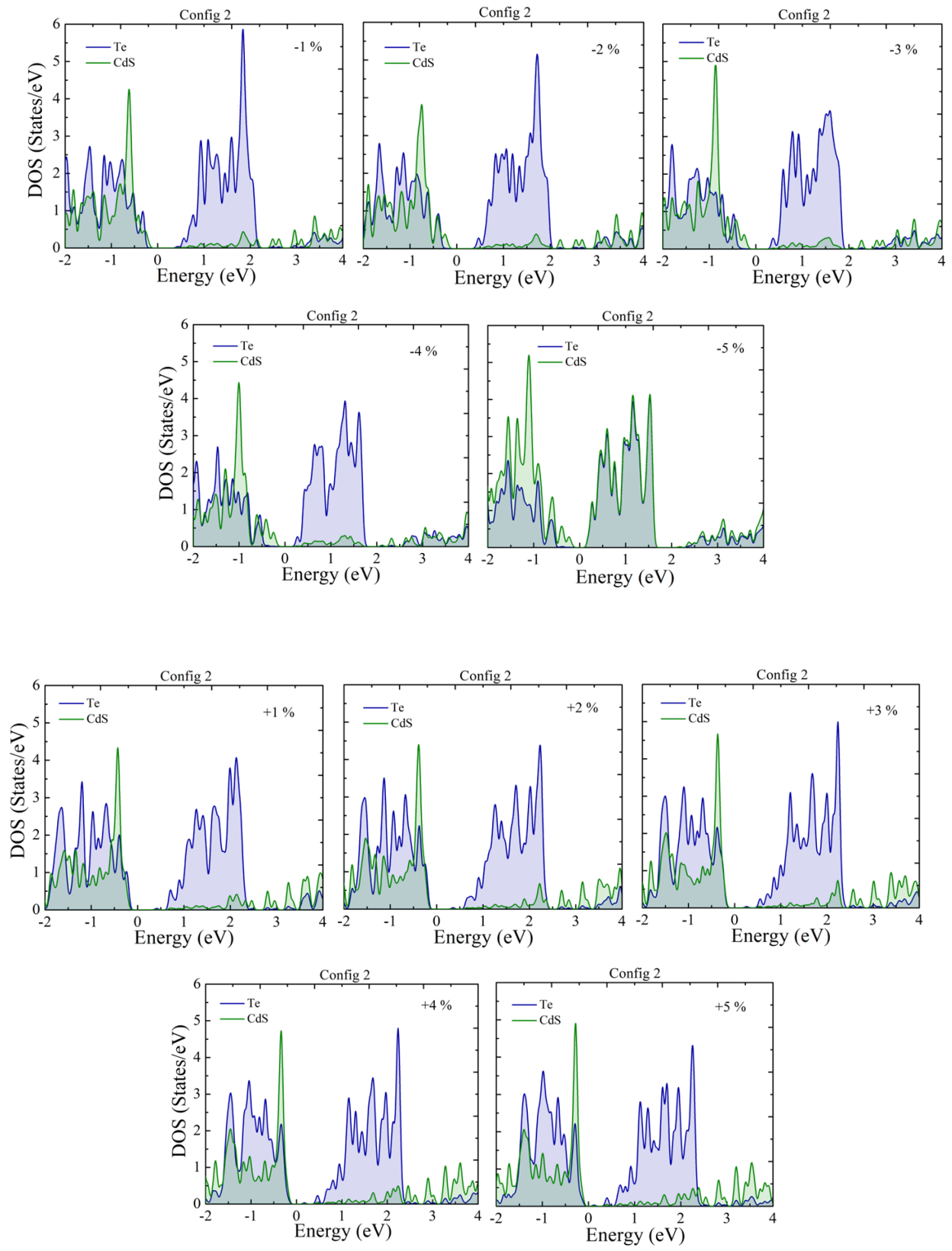


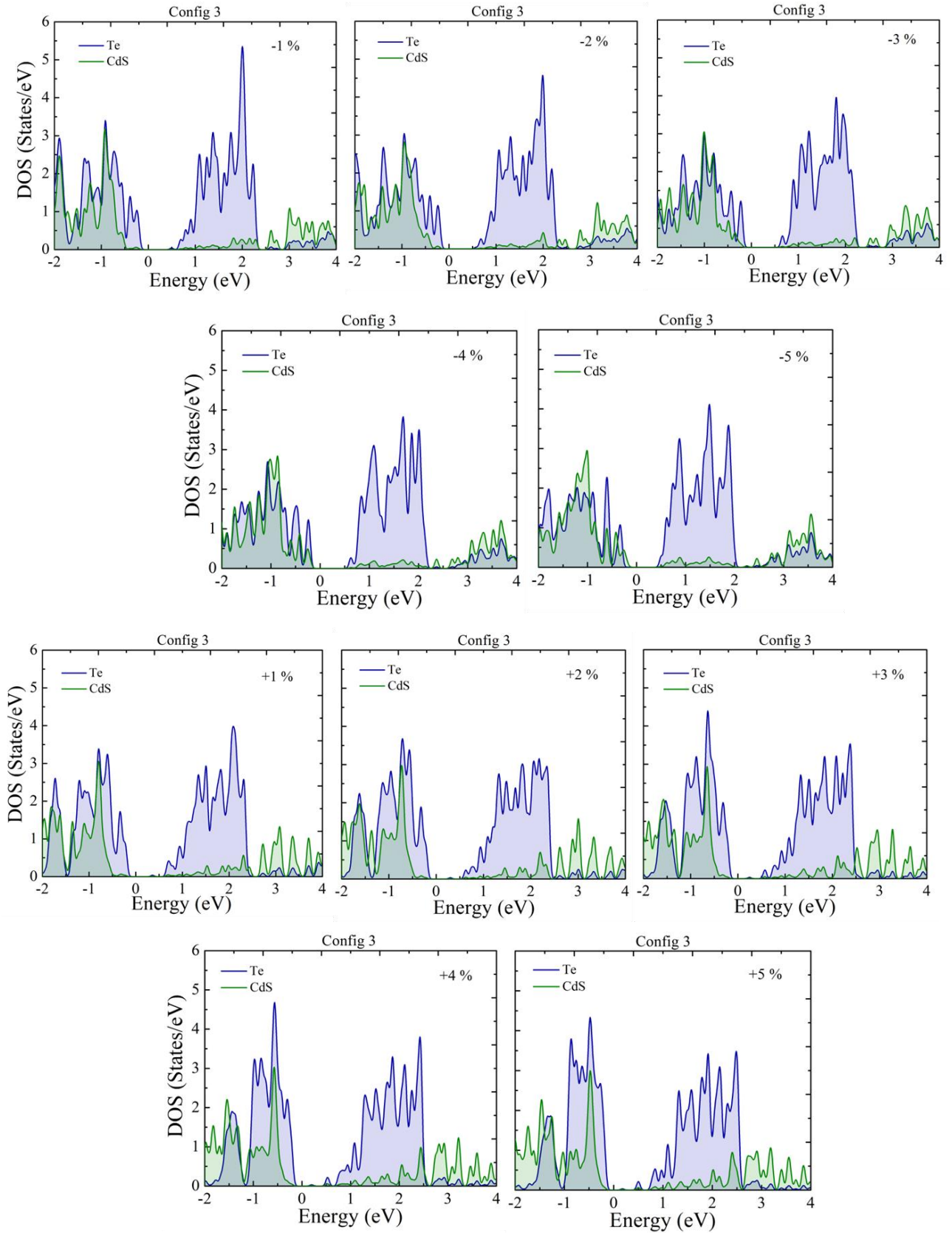
SFig. 3: Planar averaged electron density difference in the three configurations of the CdS- $\alpha$ -Te heterostructure. Vertical dashed lines mark the CdS and  $\alpha$ -Te regions. The positive and negative values represent the electron accumulation and depletion respectively.

STable 3: Interlayer distance variation with reference to applied biaxial strain in the three configurations of the CdS-  $\alpha$ -Te heterostructure.

Strain (%)	Interlayer distance ( $\text{\AA}$ )		
	Config-1	Config-2	Config-3
-5	-	3.00	3.10
-4	3.43	3.08	3.13
-3	3.47	3.14	3.16
-2	3.51	3.19	3.18
-1	3.55	3.23	3.21
0	3.59	3.23	3.25
1	3.62	3.27	3.24
2	3.65	3.26	3.25
3	3.67	3.25	3.24
4	3.69	3.23	3.22
5	-	3.20	3.20

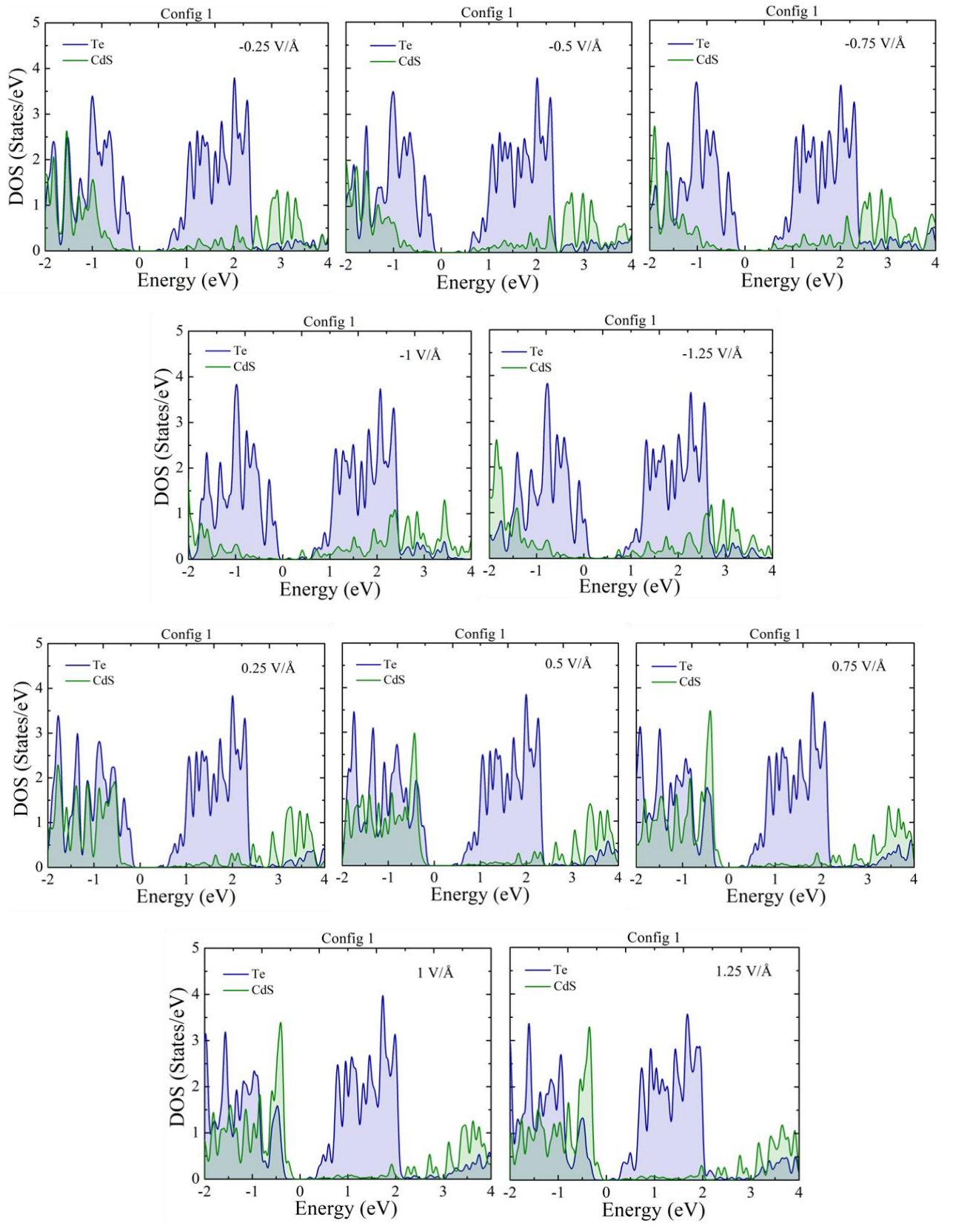


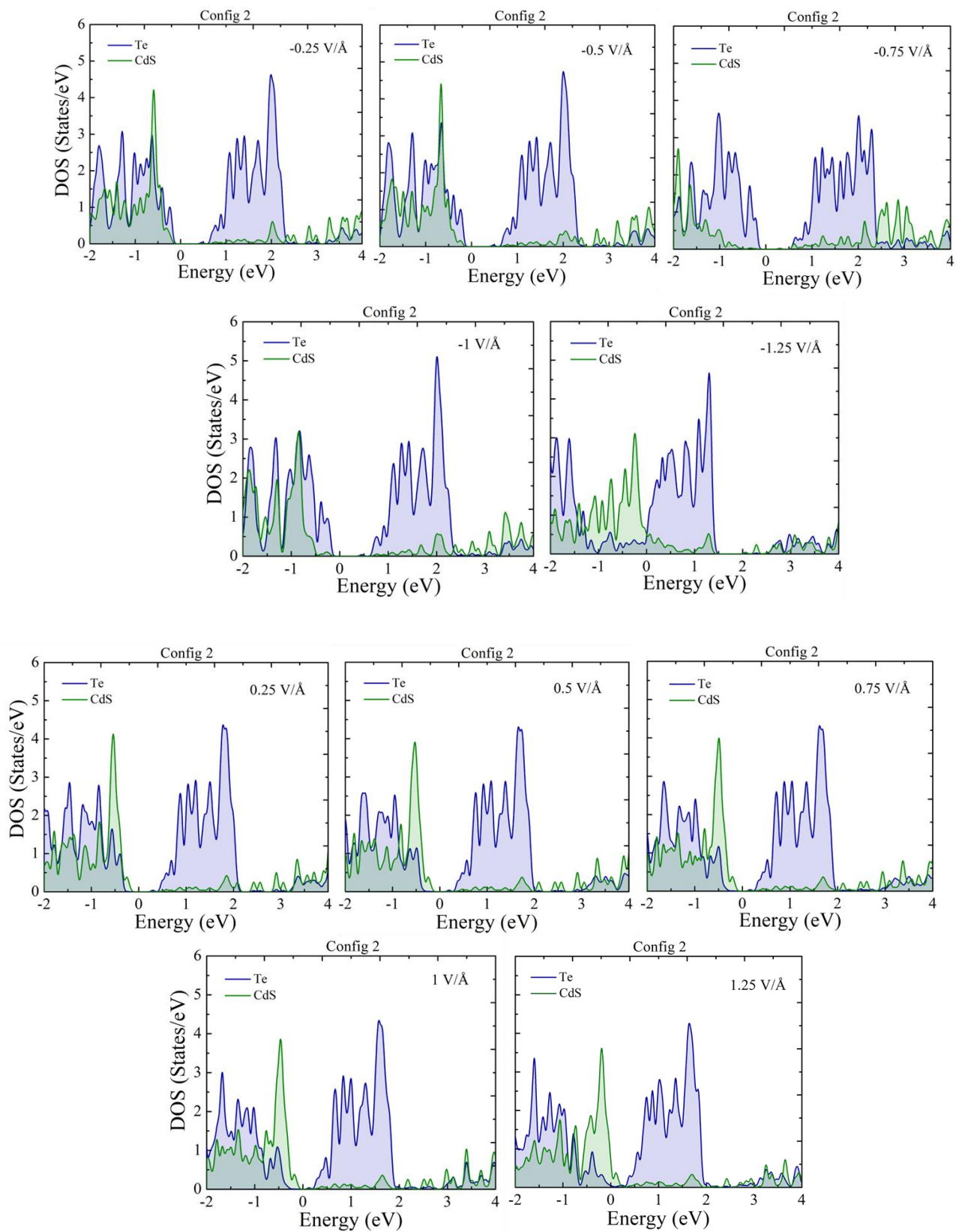


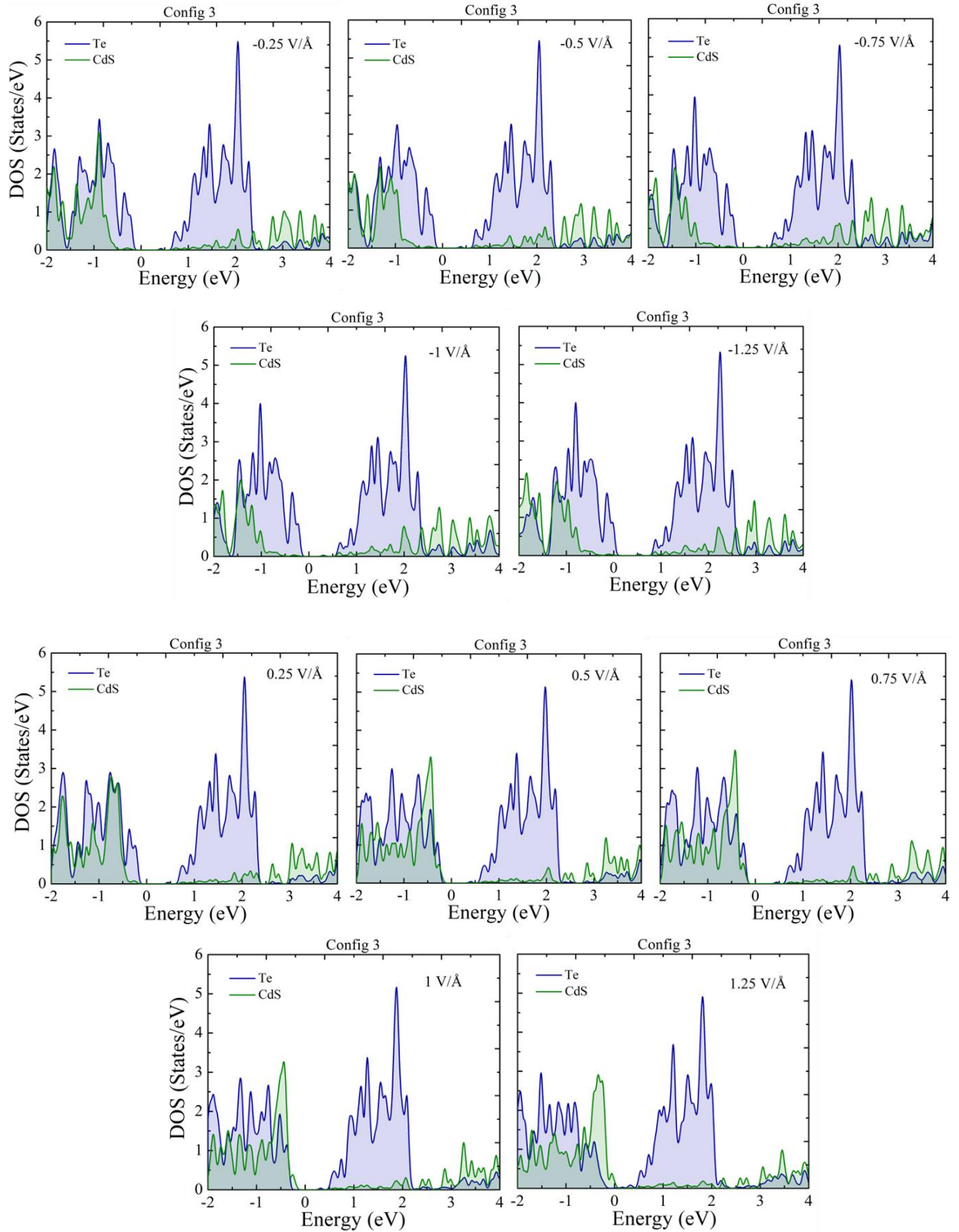


SFig 4: The evolution of layer resolved density (LDOS) of states of the three configurations of the CdS- $\alpha$ -Te heterostructure with respect to applied biaxial strain. The negative and positive strain values represent the compression and tension respectively. The Fermi-level is set to zero.



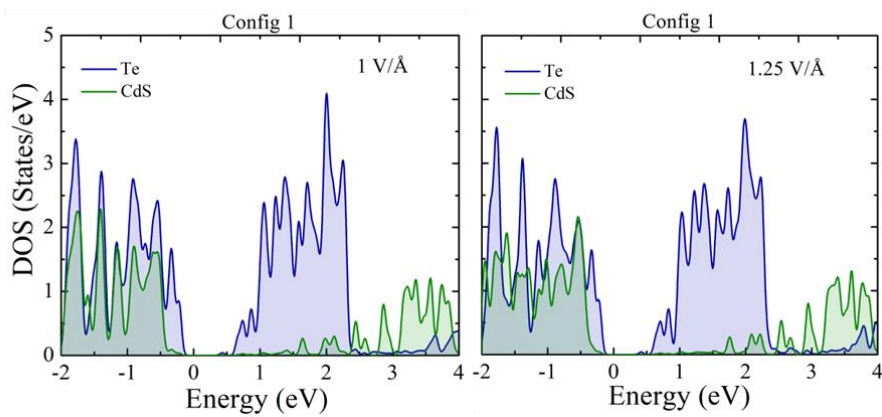
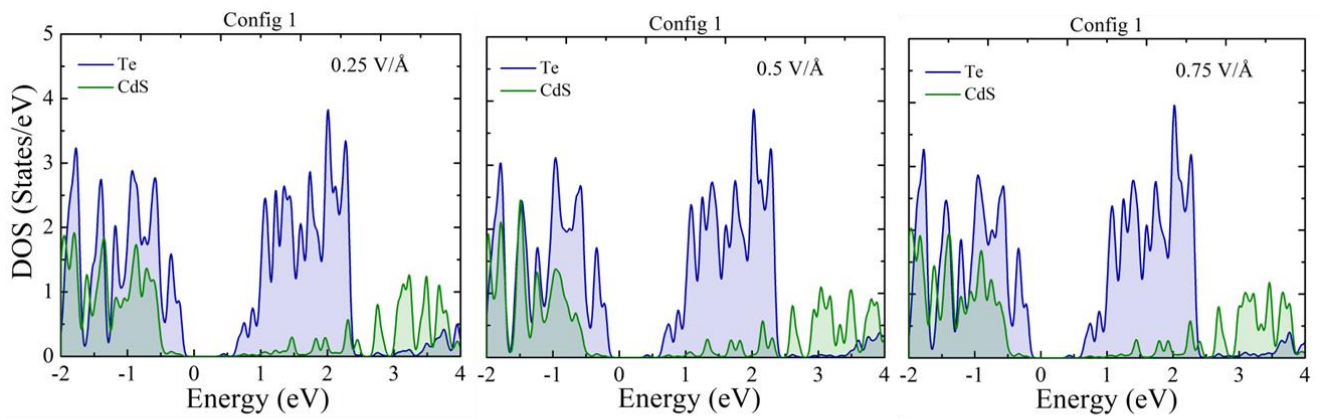
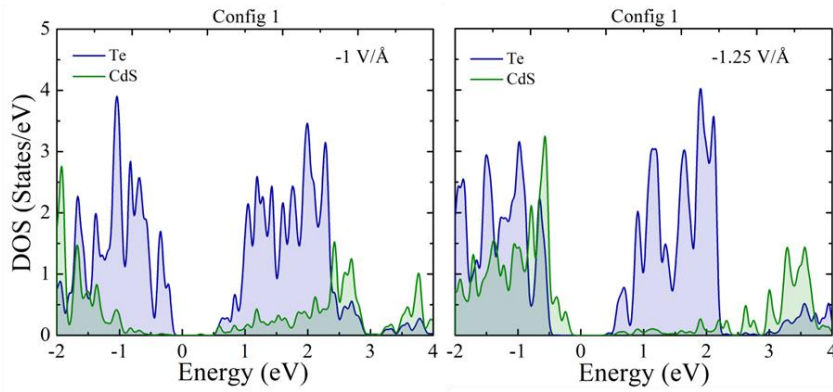
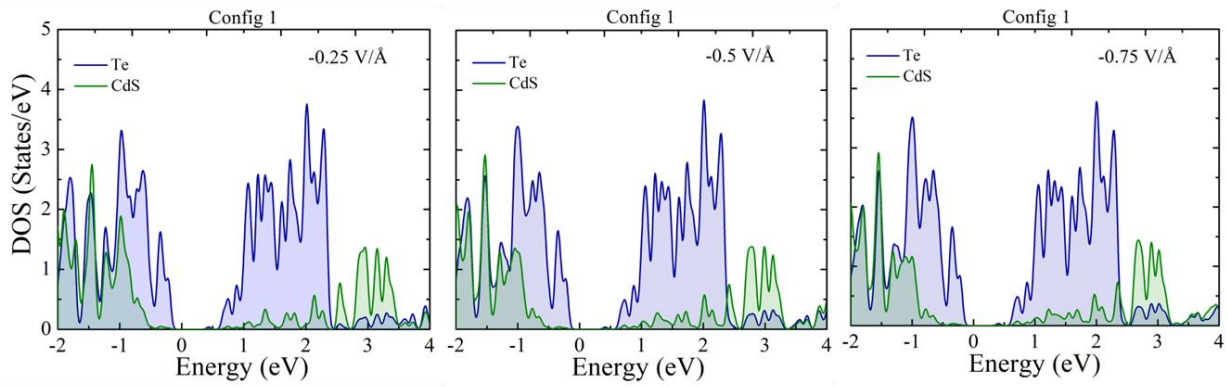


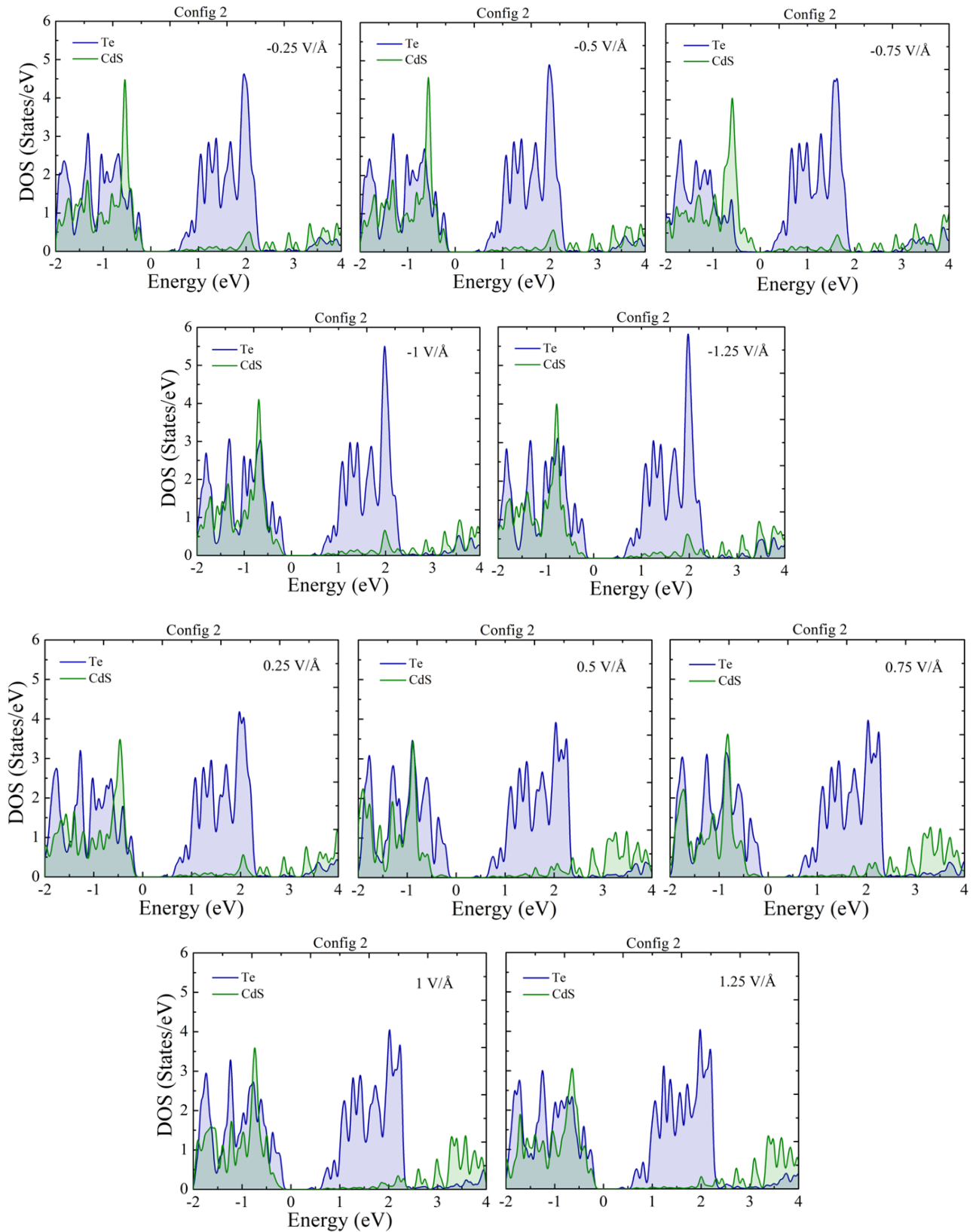


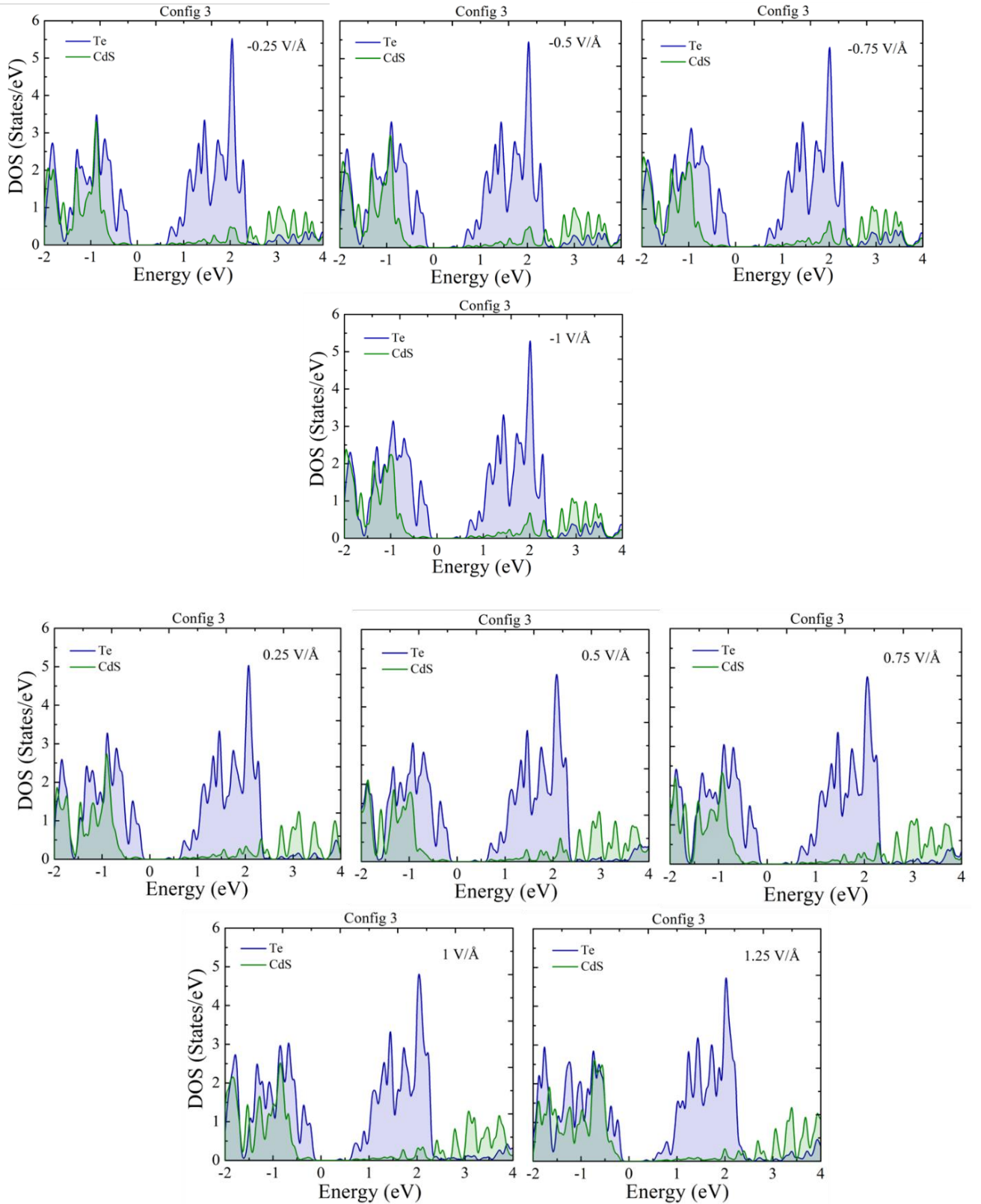


SFig. 5: The evolution of layer resolved density of states of the three configurations of the CdS- $\alpha$ -Te interface with respect to applied electric field. The negative and positive electric field values represent the direction of the fields pointing along negative and positive z-axis, respectively. The Fermi-level is set to zero. These are the results when the ionic relaxation is not performed.









SFig. 6: The evolution of layer resolved density of states of the CdS- $\alpha$ -Te heterostructure with respect to applied electric field. The negative and positive electric field values represent the direction of the fields pointing along negative and positive z-axis, respectively. The Fermi-level is set to zero. These are the results when the ionic relaxation is performed.